TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2 S C 5 2 6 3

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

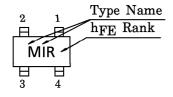
Low Noise Figure : NF = 1.7dB (f = 2GHz)

High Gain : Gain = 11dB (f = 2GHz)

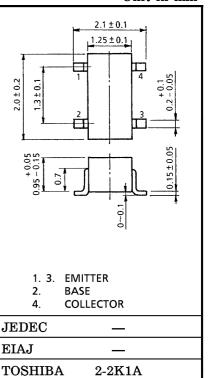
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	15	V
Collector-Emitter Voltage	v_{CEO}	7	V
Emitter-Base Voltage	$v_{ m EBO}$	1.5	V
Collector Current	$I_{\mathbf{C}}$	15	mA
Base Current	$I_{\mathbf{B}}$	7	mA
Collector Power Dissipation	PC	100	mW
Junction Temperature	$T_{ m j}$	125	°C
Storage Temperature Range	$\mathrm{T}_{\mathrm{stg}}$	-55~125	$^{\circ}\mathrm{C}$

MARKING



Unit in mm



Weight: 0.006g

MICROWAVE CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	$ m f_T$	$V_{CE} = 5V, I_{C} = 7mA$	9	12	_	GHz
Incortion (ioin	$ S_{21e} ^2(1)$	$V_{CE}=5V$, $I_{C}=7mA$, $f=1GHz$	14	17	_	dB
	$ S_{21e} ^2$ (2)	$V_{CE}=5V$, $I_{C}=7mA$, $f=2GHz$	8	11		
I Noise Figure	NF (1)	$V_{CE}=5V$, $I_{C}=3mA$, $f=1GHz$		1.3		dB
	NF (2)	$V_{CE}=5V$, $I_{C}=3mA$, $f=2GHz$	_	1.7	3	ub

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	$V_{CB} = 10V, I_{E} = 0$	_	_	1	μ A
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 1V, I_C = 0$	_	_	1	μ A
DC Current Gain	h _{FE} (Note 1)	$V_{\rm CE}$ =5V, $I_{\rm C}$ =7mA	60	_	160	
Output Capacitance	C_{ob}	$V_{\mathrm{CB}} = 5 \mathrm{V}, \ \mathrm{I_E} = 0, \ \mathrm{f} = 1 \mathrm{MHz}$		0.45	_	pF
Reverse Transfer Capacitance	$\mathrm{C_{re}}$	(Note 2)		0.35	0.75	рF

(Note 1): hFE Classification $R:50{\sim}100,~O:80{\sim}160$ (Note 2): C_{re} is measured by 3 terminal method with capacitance bridge.